

Symbol	Test Conditions	Characteristic Values		
	(T _J = 25°C, unless otherwise specified)	Min.	Typ.	Max.
R _{DS(on)}	V _{GS} = 10 V, I _D = 0.5 I _{D25}	21N50		0.25 Ω
		24N50		0.23 Ω
		26N50		0.20 Ω
	Pulse test, t ≤ 300 μs, duty cycle d ≤ 2 %			
g _{fs}	V _{DS} = 10 V; I _D = 0.5 I _{D25} , pulse test	11	21	S
C _{iss}	V _{GS} = 0 V, V _{DS} = 25 V, f = 1 MHz		4200	pF
C _{oss}			450	pF
C _{rss}			135	pF
t _{d(on)}	V _{GS} = 10 V, V _{DS} = 0.5 V _{DSS} , I _D = 0.5 I _{D25} R _G = 2 Ω (External)		16	25 ns
t _r			33	45 ns
t _{d(off)}			65	80 ns
t _f			30	40 ns
Q _{g(on)}	V _{GS} = 10 V, V _{DS} = 0.5 V _{DSS} , I _D = 0.5 I _{D25}		135	160 nC
Q _{gs}			28	40 nC
Q _{gd}			62	85 nC
R _{thJC}	(TO-247 Case Style)		0.25	0.42 K/W
R _{thCK}				K/W

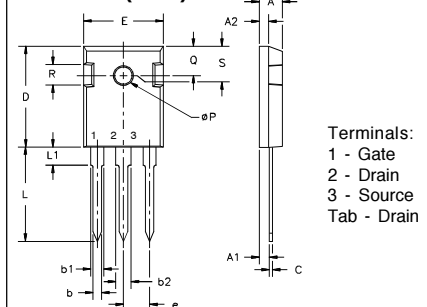
Source-Drain Diode

Characteristic Values
(T_J = 25°C, unless otherwise specified)

Symbol	Test Conditions	Min.	Typ.	Max.
I _S	V _{GS} = 0 V	21N50		21 A
		24N50		24 A
		26N50		26 A
I _{SM}	Repetitive; pulse width limited by T _{JM}	21N50		84 A
		24N50		96 A
		26N50		104 A
V _{SD}	I _F = I _S , V _{GS} = 0 V, Pulse test, t ≤ 300 μs, duty cycle d ≤ 2 %			1.5 V
t _{rr}	I _F = I _S -di/dt = 100 A/μs, V _R = 100 V			T _J = 25°C 250 ns
				T _J = 125°C 400 ns
Q _{RM}				T _J = 25°C 1 μC
				T _J = 125°C 2 μC
I _{RM}				T _J = 25°C 10 A
				T _J = 125°C 15 A

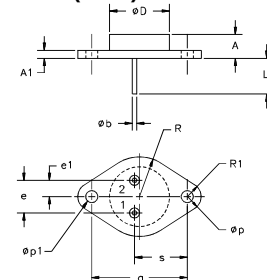
Note 1: Add "S" suffix for TO-247 SMD package option (ex: IXFH24N50S)

TO-247 AD (IXFH) Outline



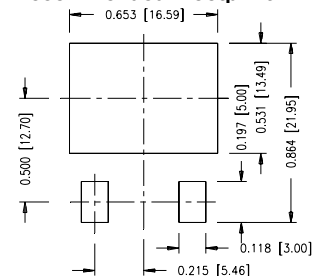
Dim.	Millimeter Min.	Millimeter Max.	Inches Min.	Inches Max.
A	4.7	5.3	.185	.209
A ₁	2.2	2.54	.087	.102
A ₂	2.2	2.6	.059	.098
b	1.0	1.4	.040	.055
b ₁	1.65	2.13	.065	.084
b ₂	2.87	3.12	.113	.123
C	.4	.8	.016	.031
D	20.80	21.46	.819	.845
E	15.75	16.26	.610	.640
e	5.20	5.72	0.205	0.225
L	19.81	20.32	.780	.800
L ₁		4.50		.177
ØP	3.55	3.65	.140	.144
Q	5.89	6.40	0.232	0.252
R	4.32	5.49	.170	.216
S	6.15	BSC	.242	BSC

TO-204 AE (IXFM) Outline

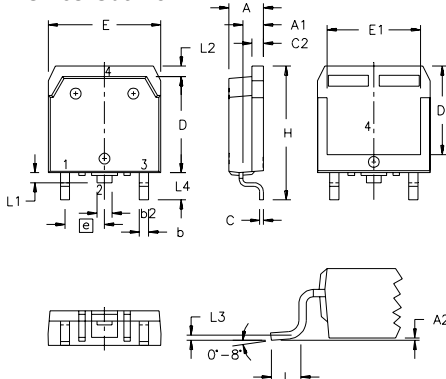


Dim.	Millimeter Min.	Millimeter Max.	Inches Min.	Inches Max.
A	6.4	11.4	.250	.450
A ₁	1.53	3.42	.060	.135
Øb	1.45	1.60	.057	.063
ØD		22.22		.875
e	10.67	11.17	.420	.440
e ₁	5.21	5.71	.205	.225
L	11.18	12.19	.440	.480
Øp	3.84	4.19	.151	.165
Øp ₁	3.84	4.19	.151	.165
q	30.15 BSC		1.187 BSC	
R	12.58	13.33	.495	.525
R ₁	3.33	4.77	.131	.188
s	16.64	17.14	.655	.675

Min. Recommended Footprint



TO-268 Outline



SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.193	.201	4.90	5.10
A ₁	.106	.114	2.70	2.90
A ₂	.001	.010	0.02	0.25
b	.045	.057	1.15	1.45
b ₂	.075	.083	1.90	2.10
C	.016	.026	0.40	0.65
C ₂	.057	.063	1.45	1.60
D	.543	.551	13.80	14.00
D ₁	.488	.500	12.40	12.70
E	.624	.632	15.85	16.05
E ₁	.524	.535	13.30	13.60
e	.215 BSC		5.45 BSC	
H	.736	.752	18.70	19.10
L	.094	.106	2.40	2.70
L ₁	.047	.055	1.20	1.40
L ₂	.039	.045	1.00	1.15
L ₃	.010 BSC		0.25 BSC	
L ₄	.150	.161	3.80	4.10

IXYS reserves the right to change limits, test conditions, and dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents: 4,835,592 4,881,106 5,017,508 5,049,961 5,187,117 5,486,715
4,850,072 4,931,844 5,034,796 5,063,307 5,237,481 5,381,025

Fig. 1 Output Characteristics

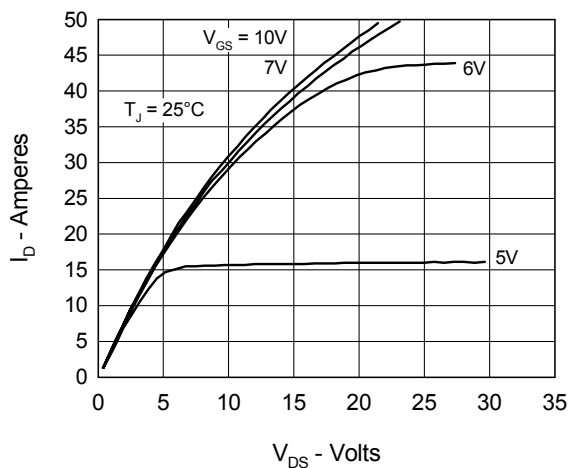


Fig. 2 Input Admittance

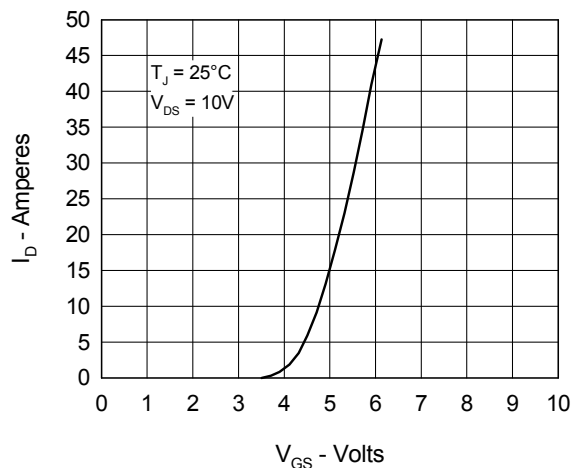
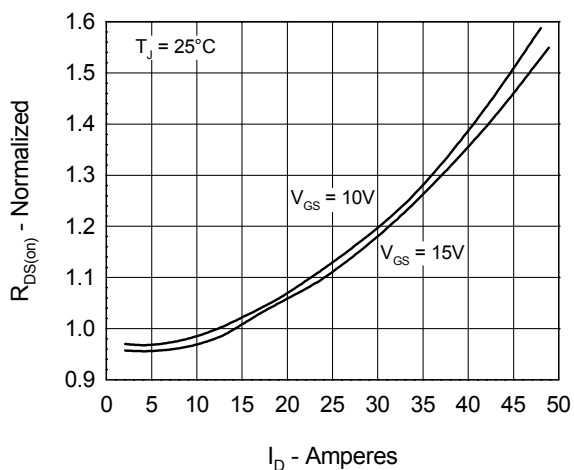

Fig. 3 $R_{DS(on)}$ vs. Drain Current


Fig. 4 Temperature Dependence of Drain to Source Resistance

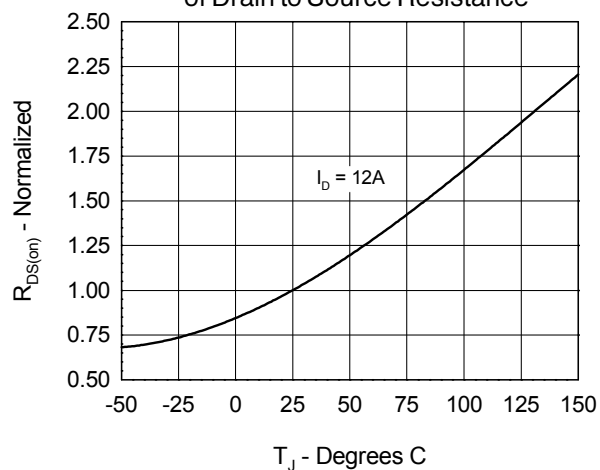


Fig. 5 Drain Current vs. Case Temperature

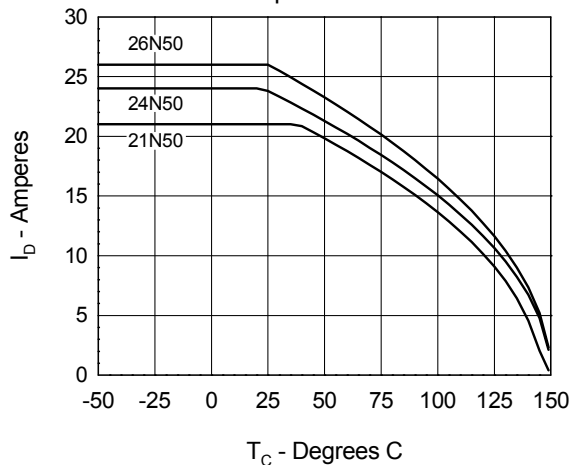


Fig. 6 Temperature Dependence of Breakdown and Threshold Voltage

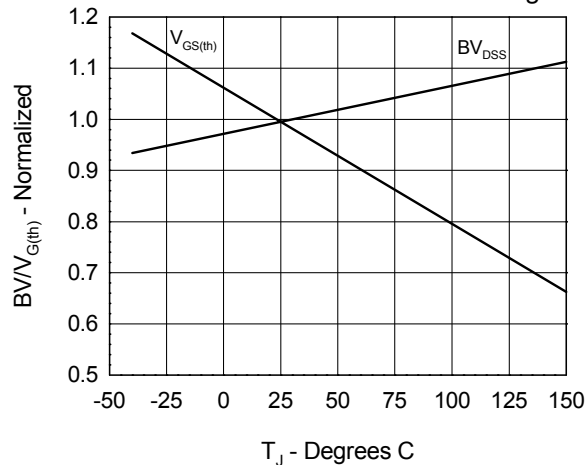


Fig.7 Gate Charge Characteristic Curve

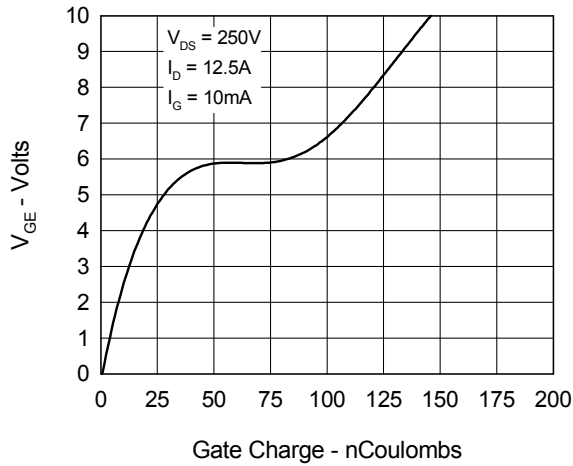


Fig.9 Capacitance Curves

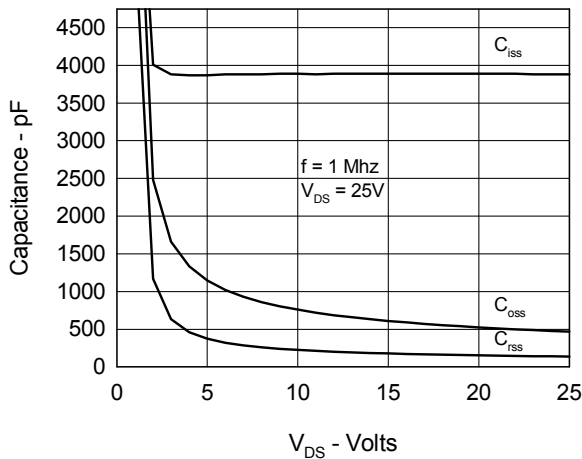


Fig.11 Transient Thermal Impedance

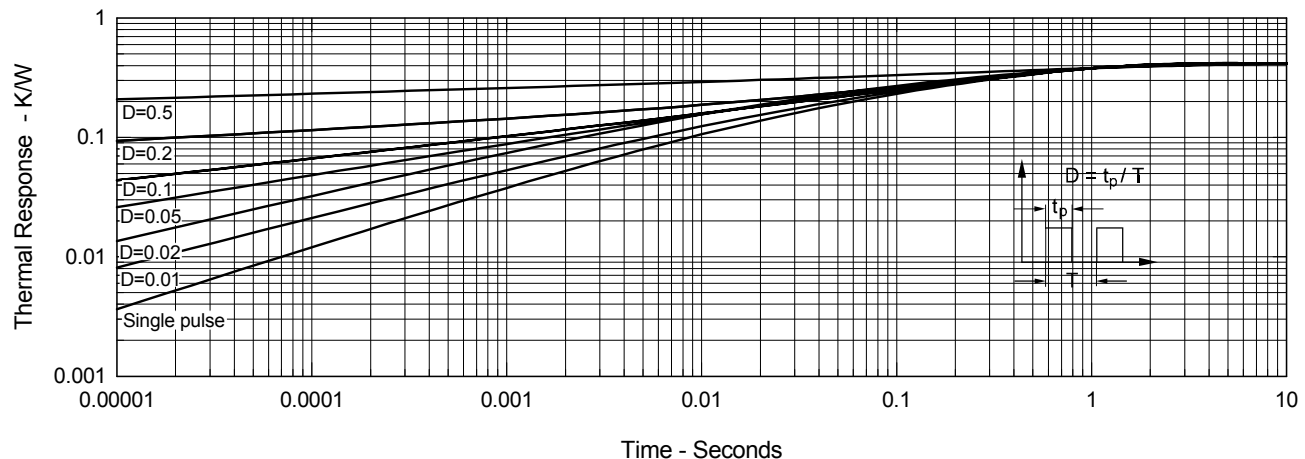


Fig.8 Forward Bias Safe Operating Area

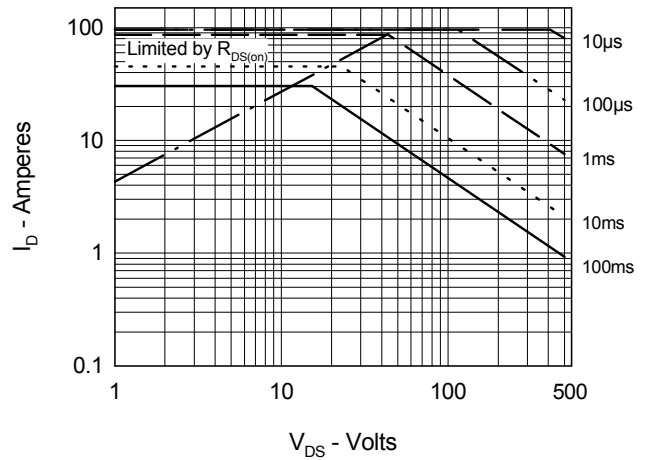
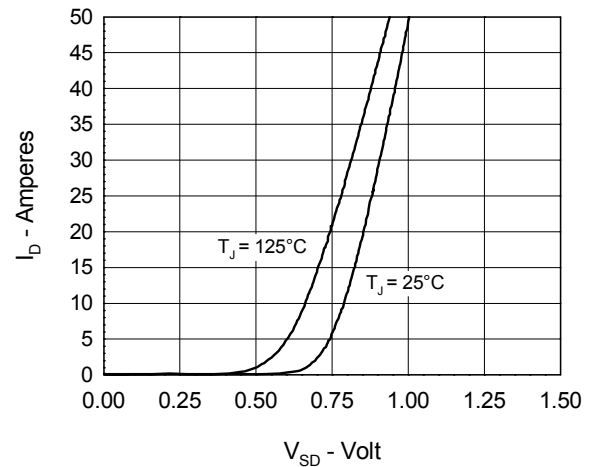


Fig.10 Source Current vs. Source to Drain Voltage





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